

FIG. 1A

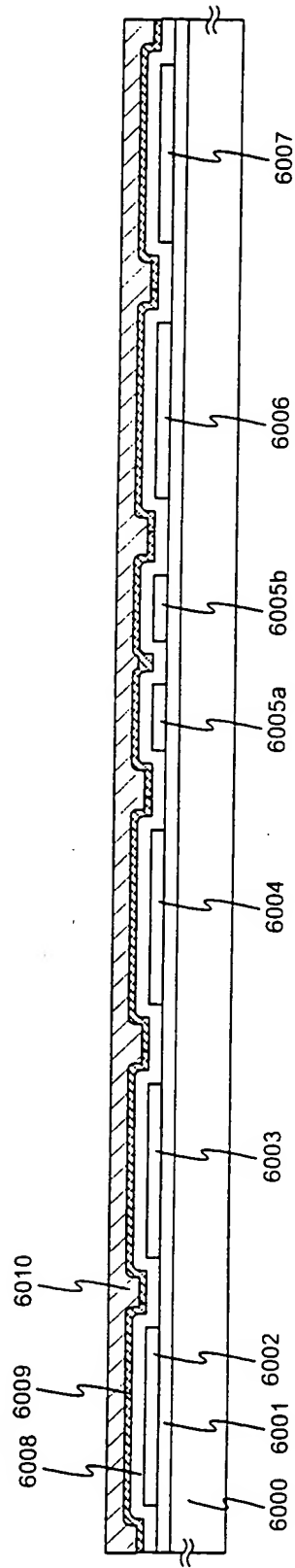


FIG. 1B

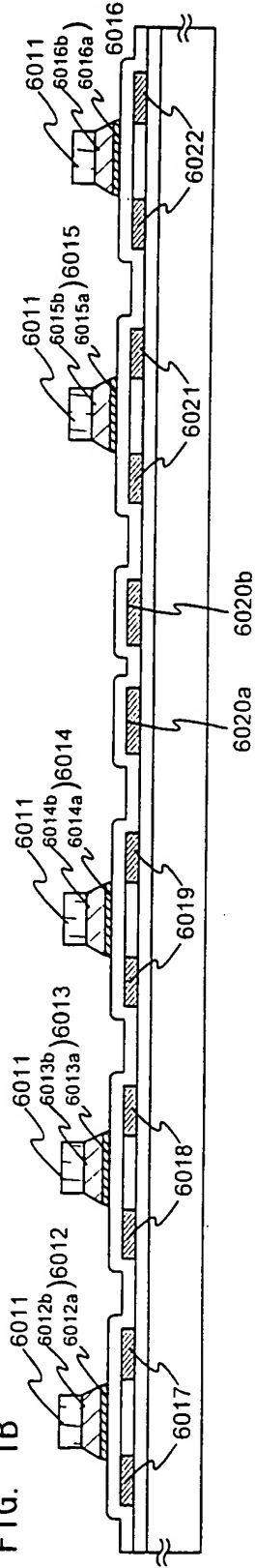


FIG. 1C

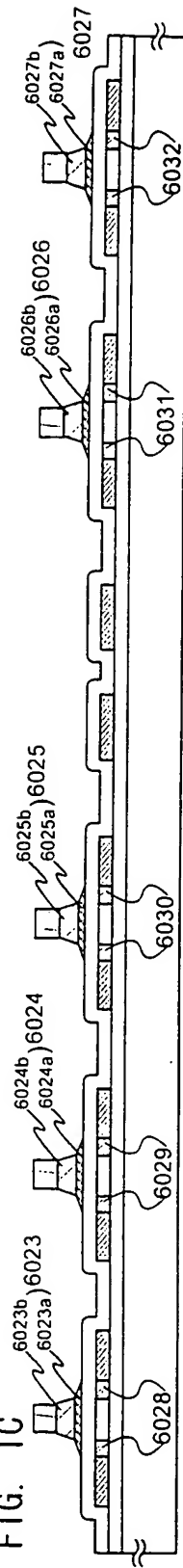


FIG. 2A

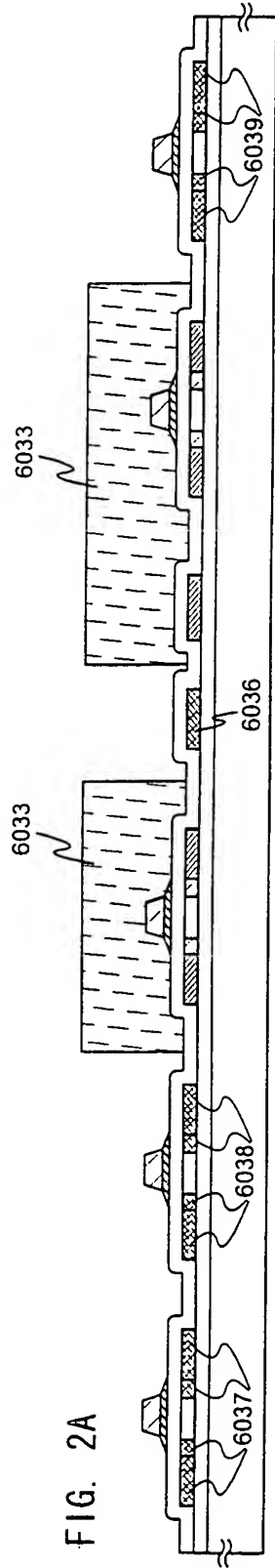


FIG. 2B

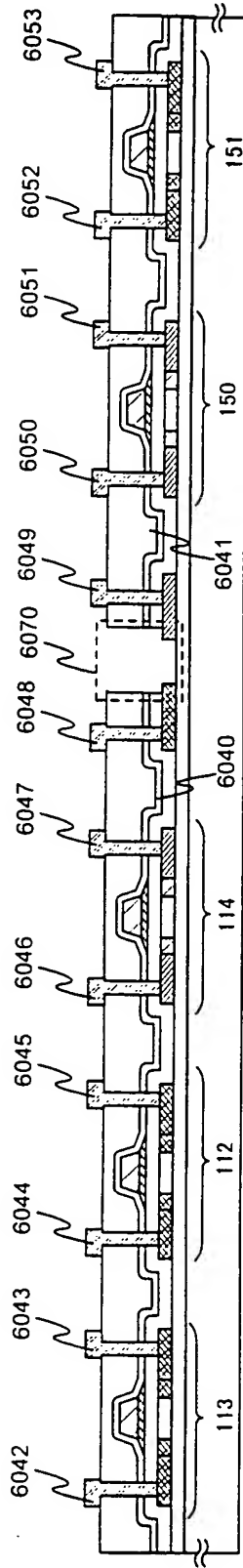
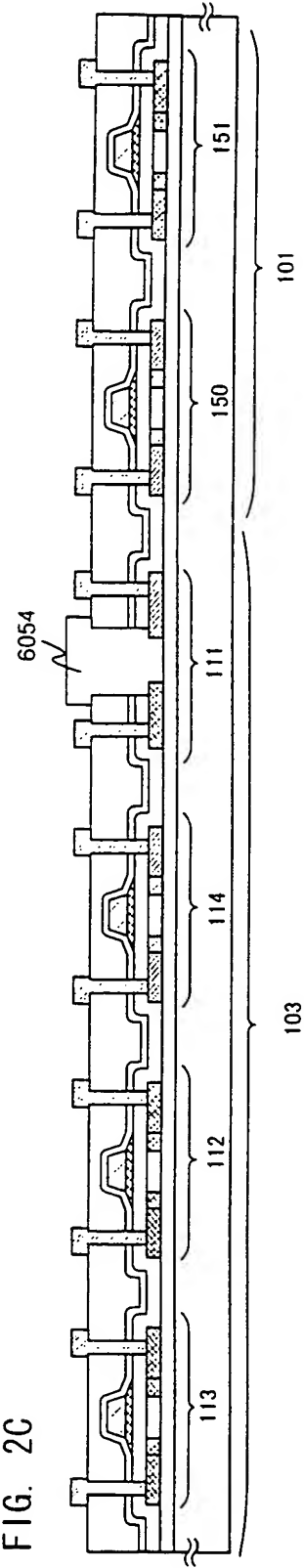


FIG. 2C



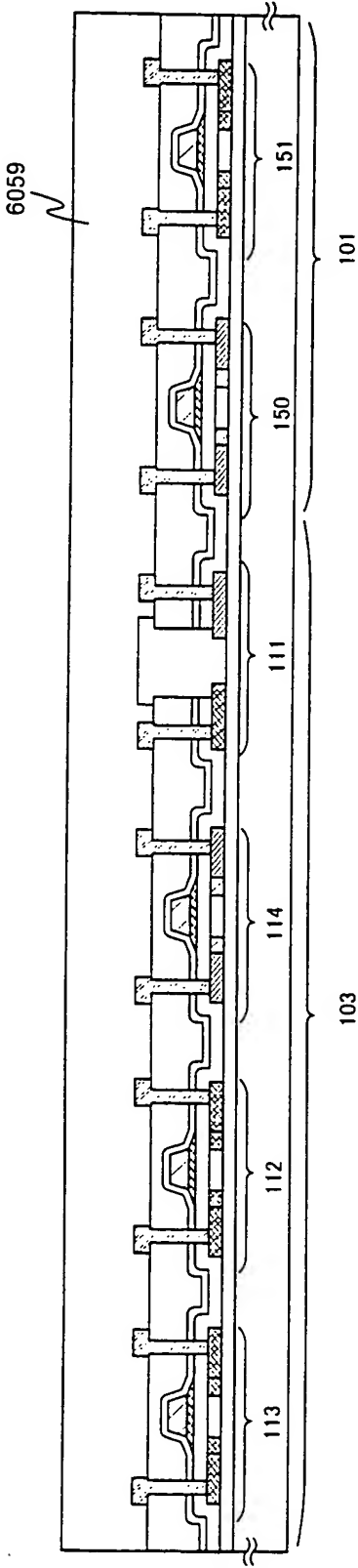


FIG. 3

FIG. 4A

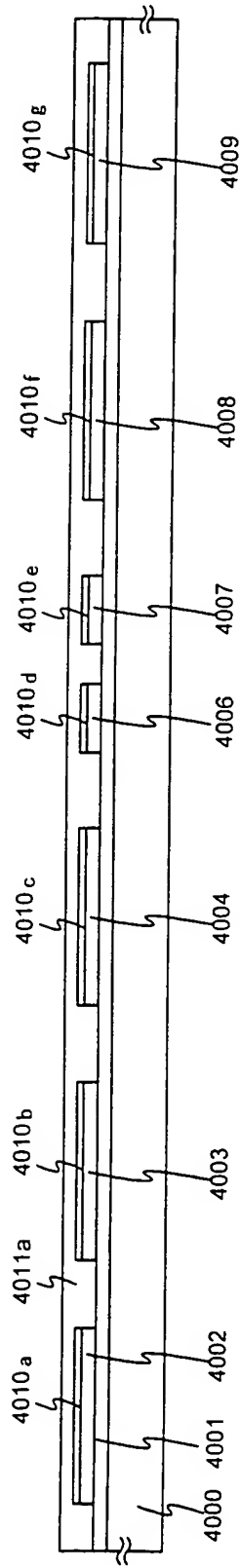


FIG. 4B

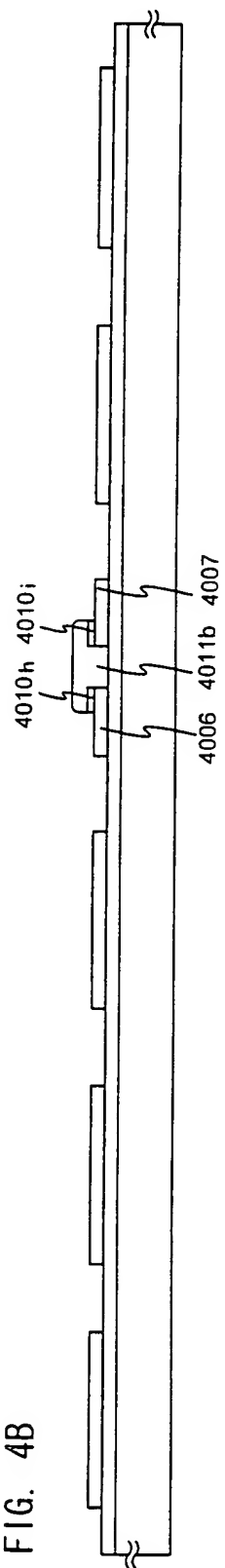


FIG. 4C

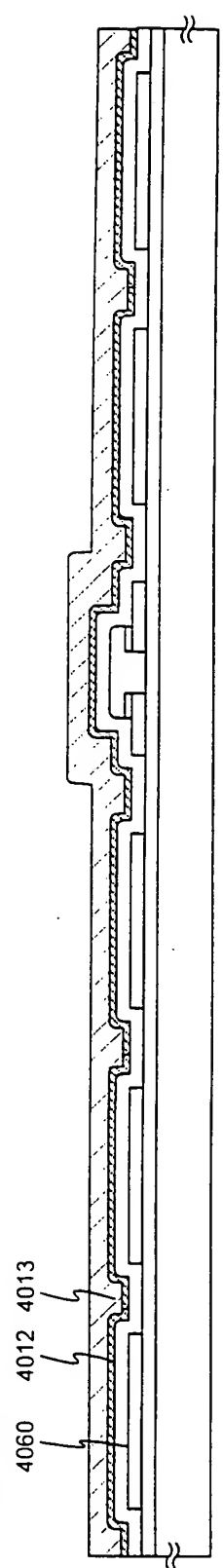


FIG. 3A

4014 4015 4016 4017 4018 4019 4020a 4021 4022 4023 4024 4025 4026a 4026b 4026c 4026d

[illegible]

FIG. 5C is a cross-sectional view of a semiconductor device. It shows a substrate with a series of rectangular blocks (4038) and a top layer (4041) with a patterned surface (4042).

FIG. 6A

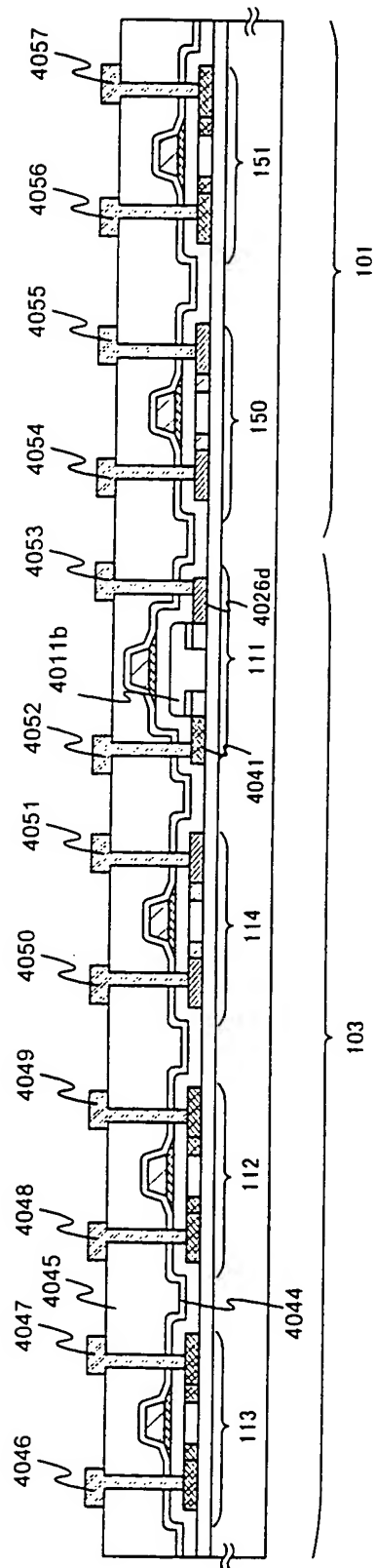


FIG. 6B

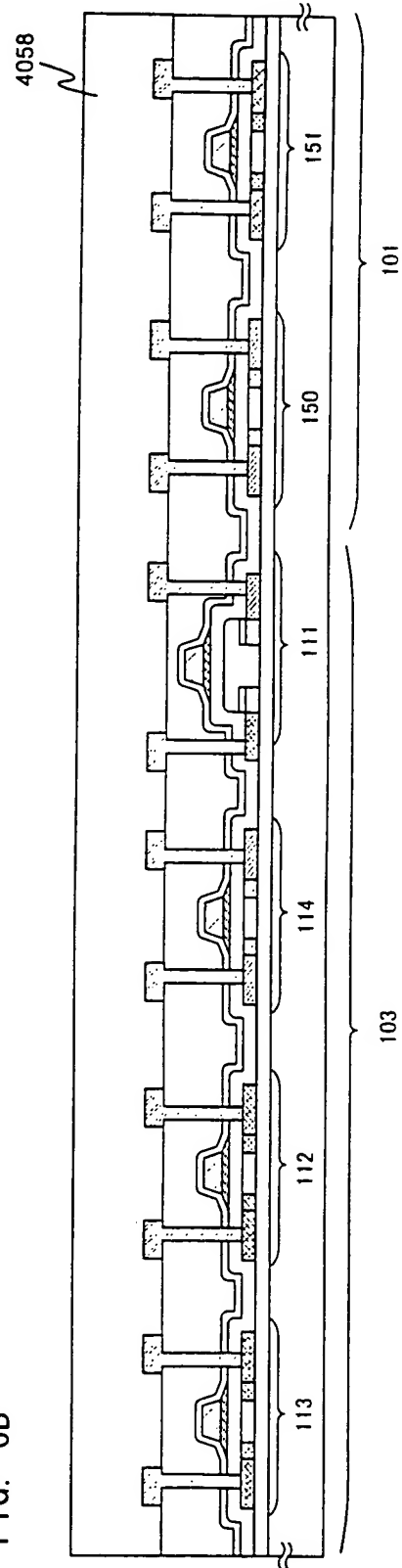


FIG. 7A

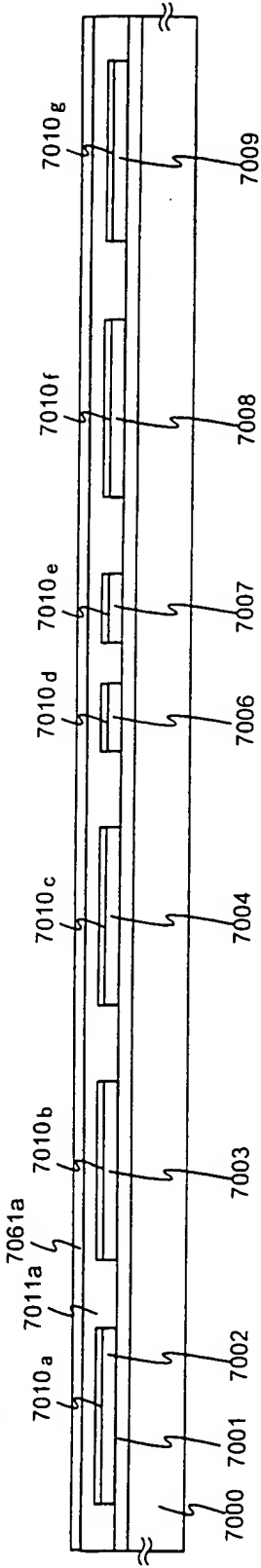


FIG. 7B

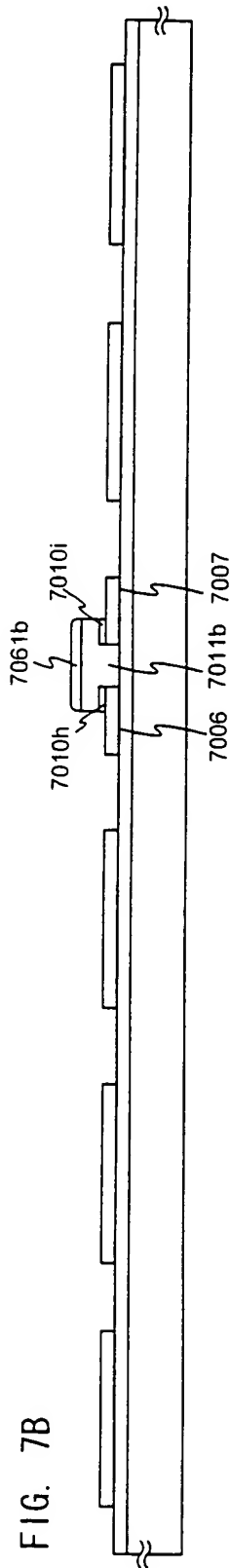


FIG. 7C

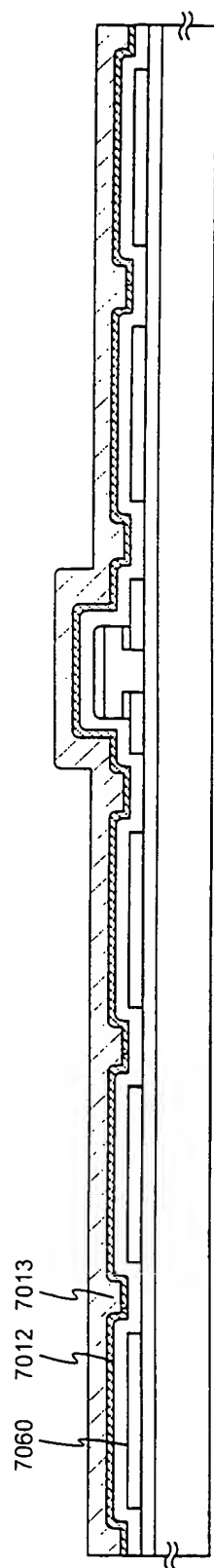


FIG. 8A

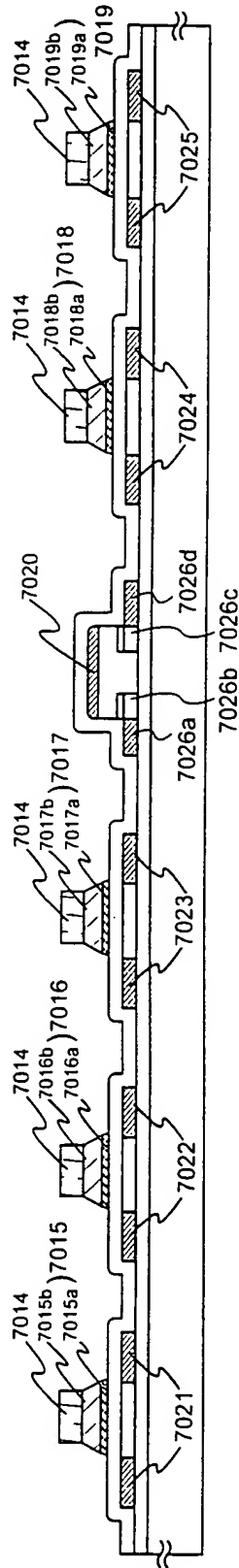


FIG. 8B

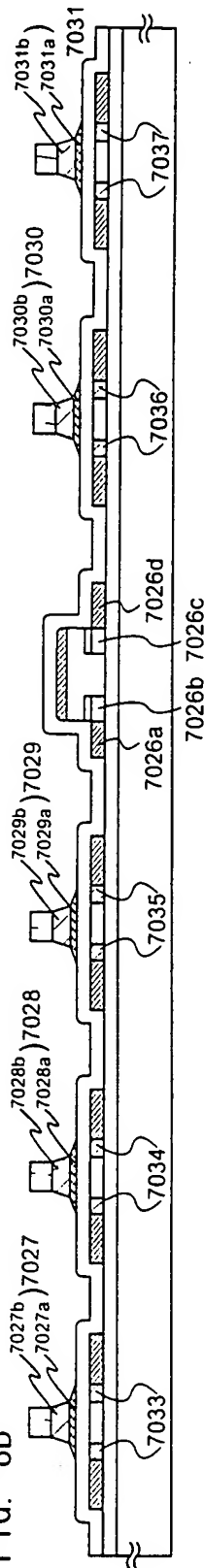


FIG. 8C

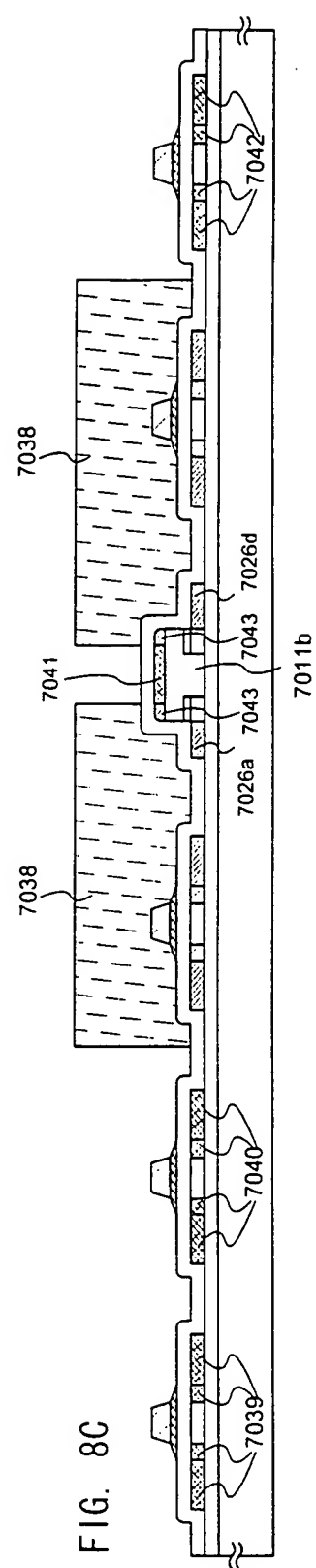




FIG. 9A

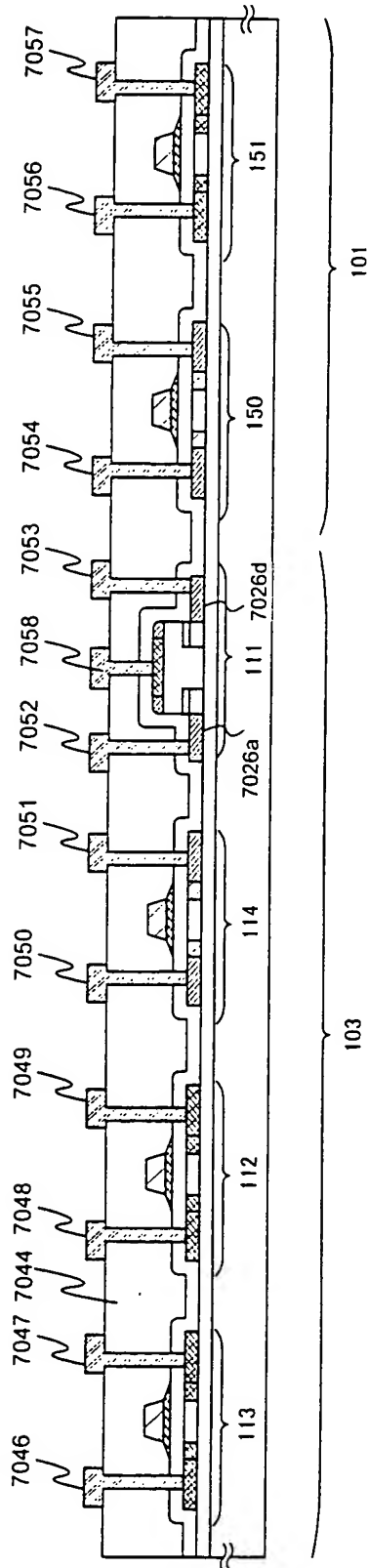
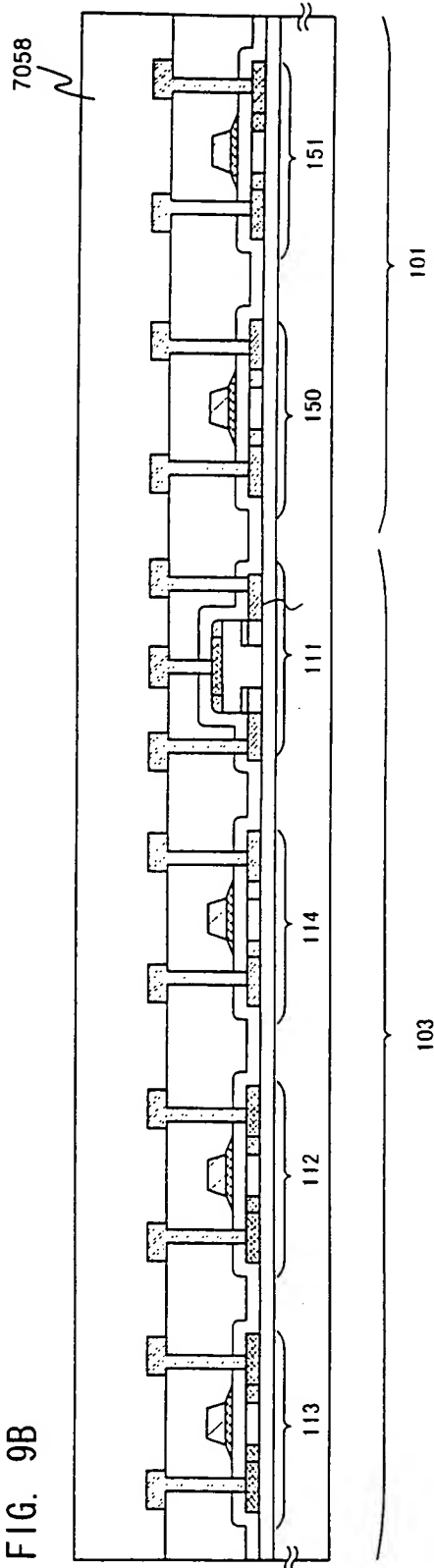


FIG. 9B



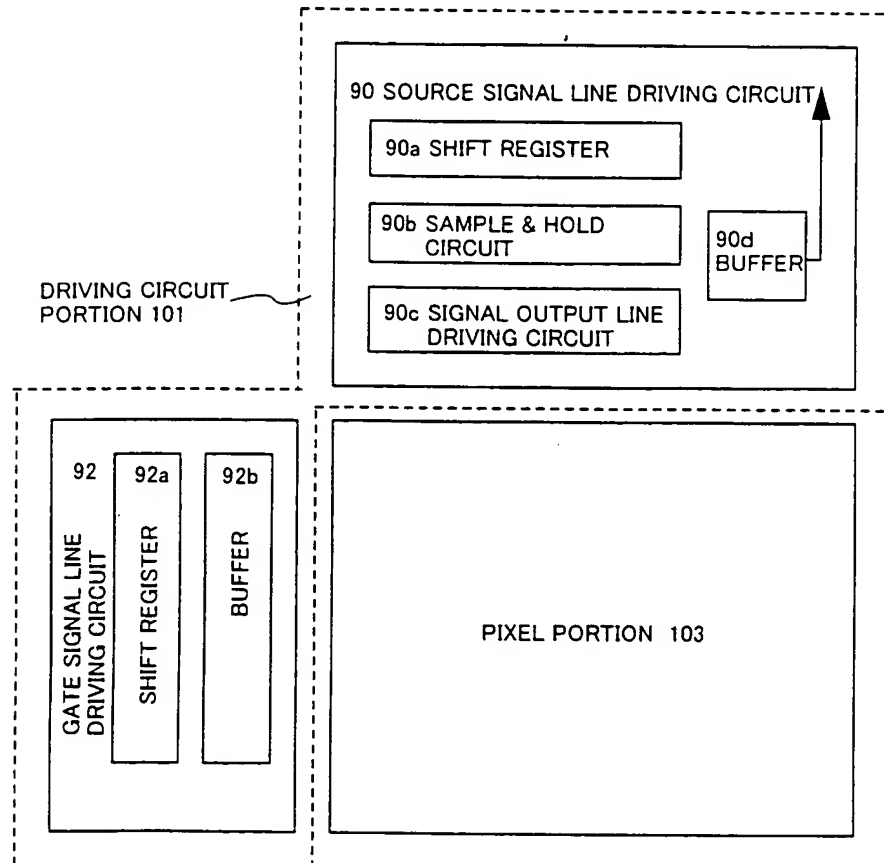


FIG. 10

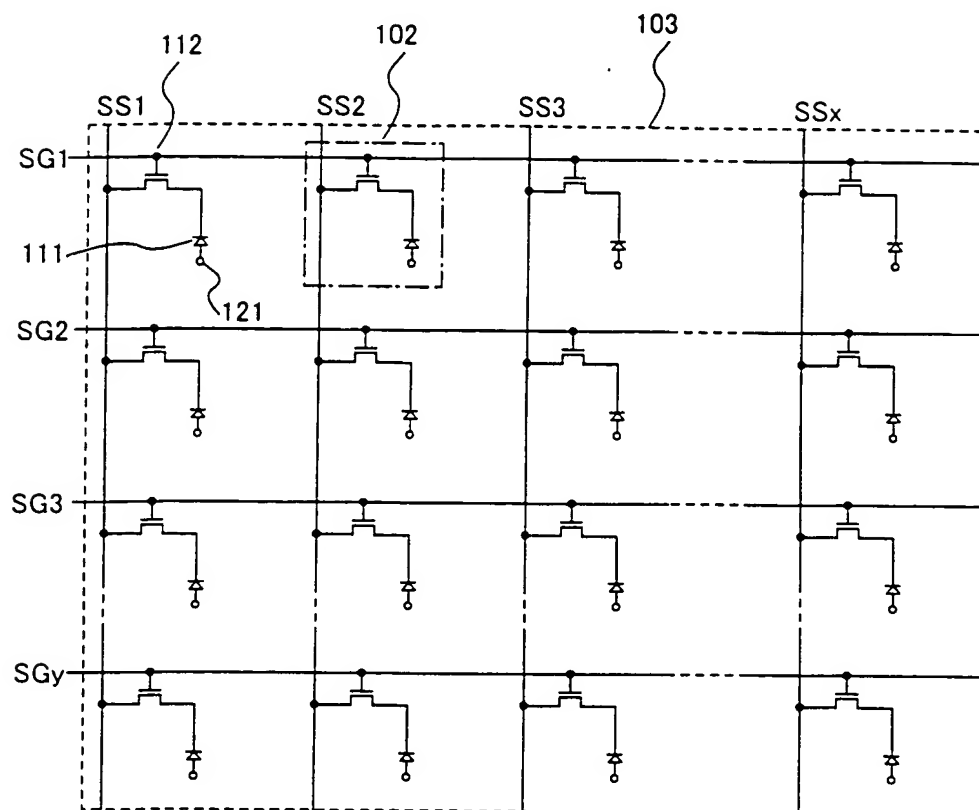


FIG. 11

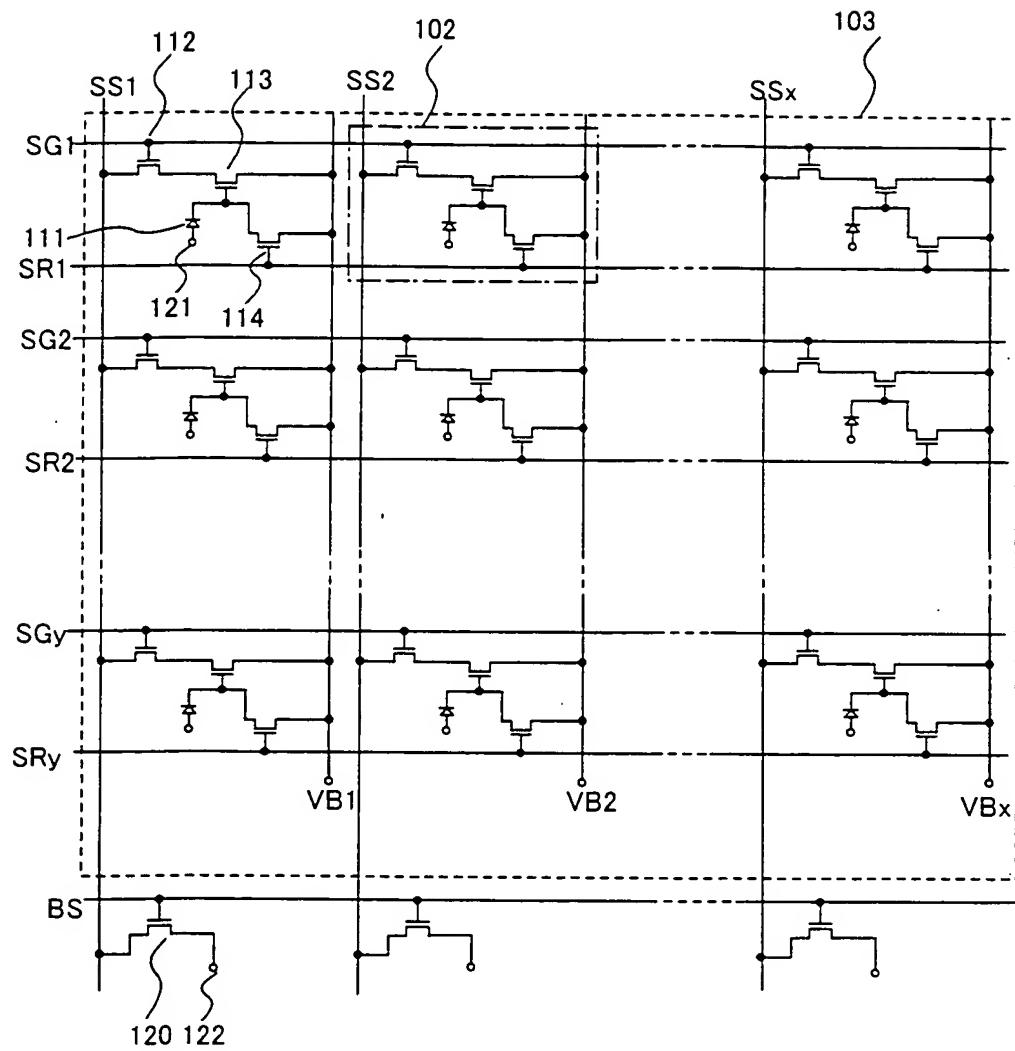


FIG. 12

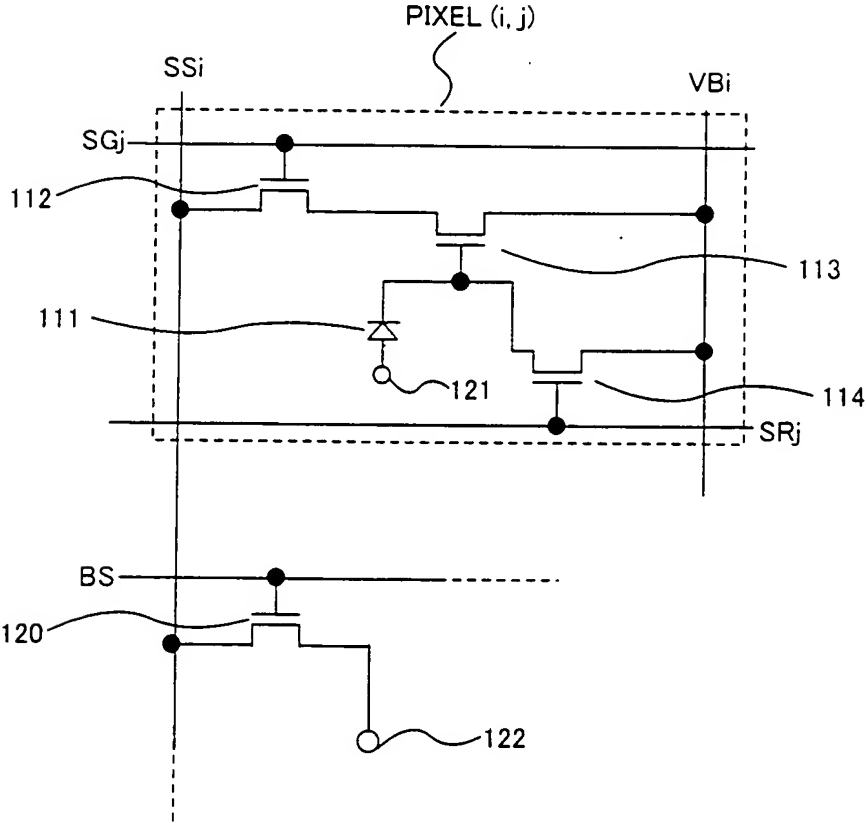


FIG. 13

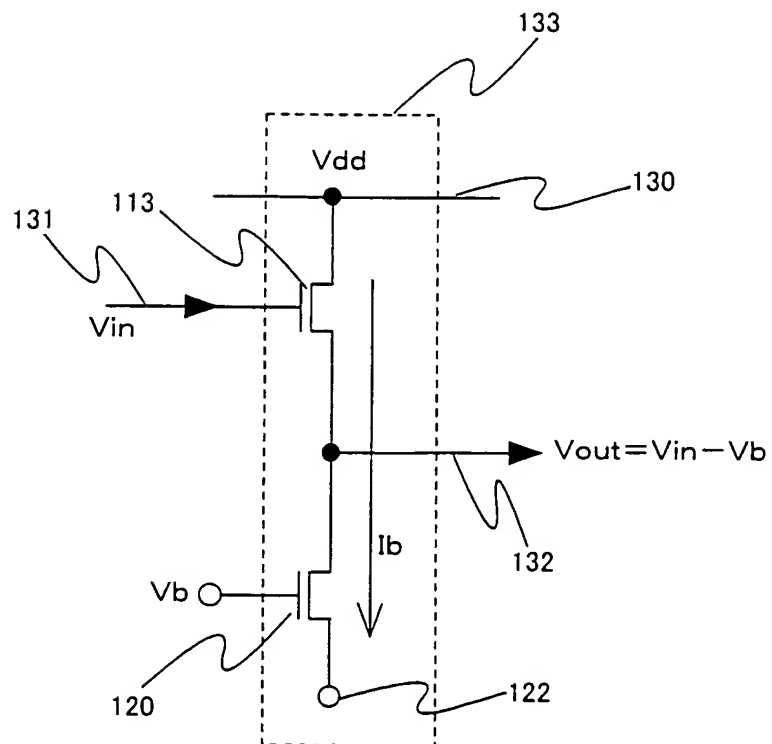


FIG. 14

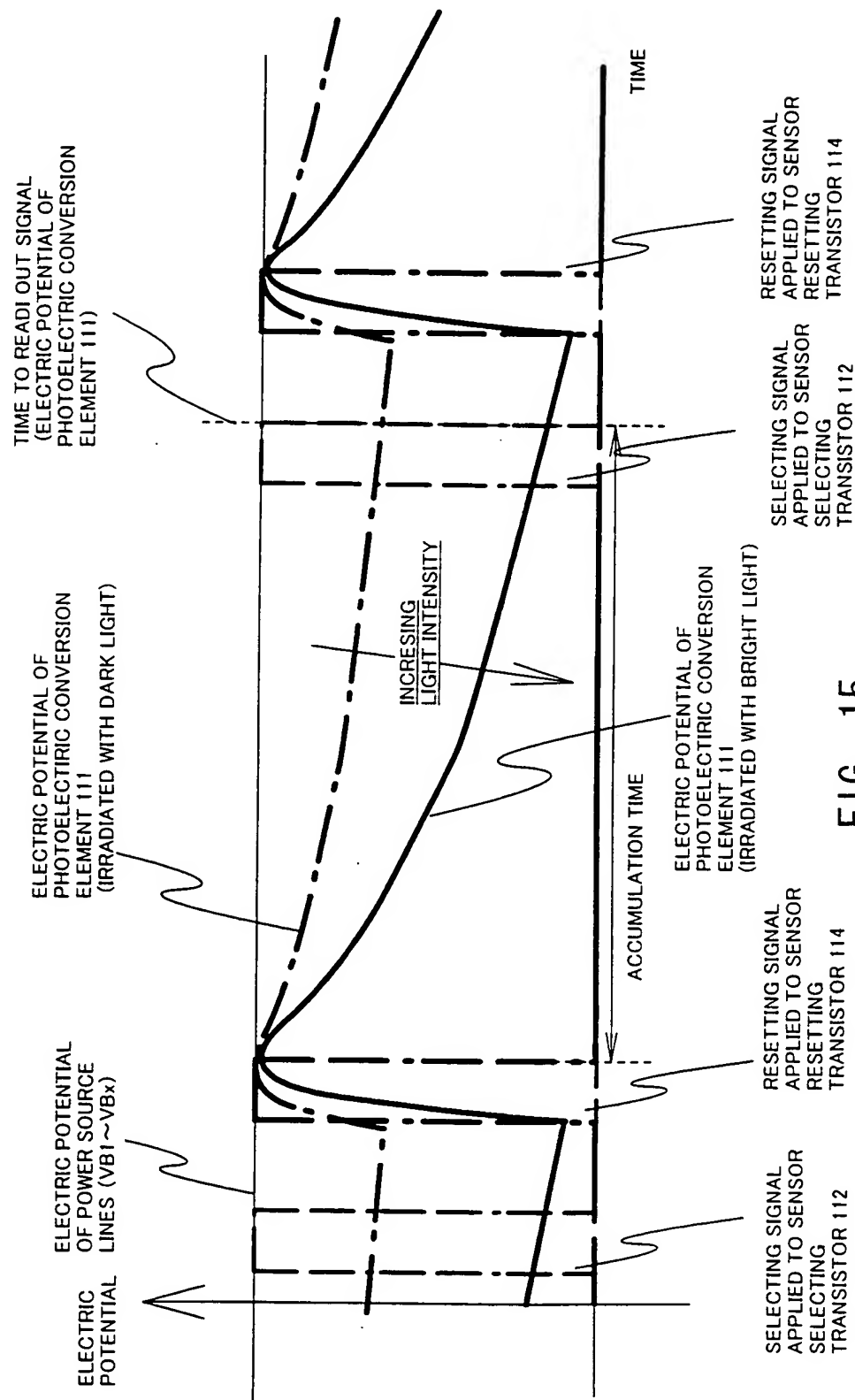


FIG. 15

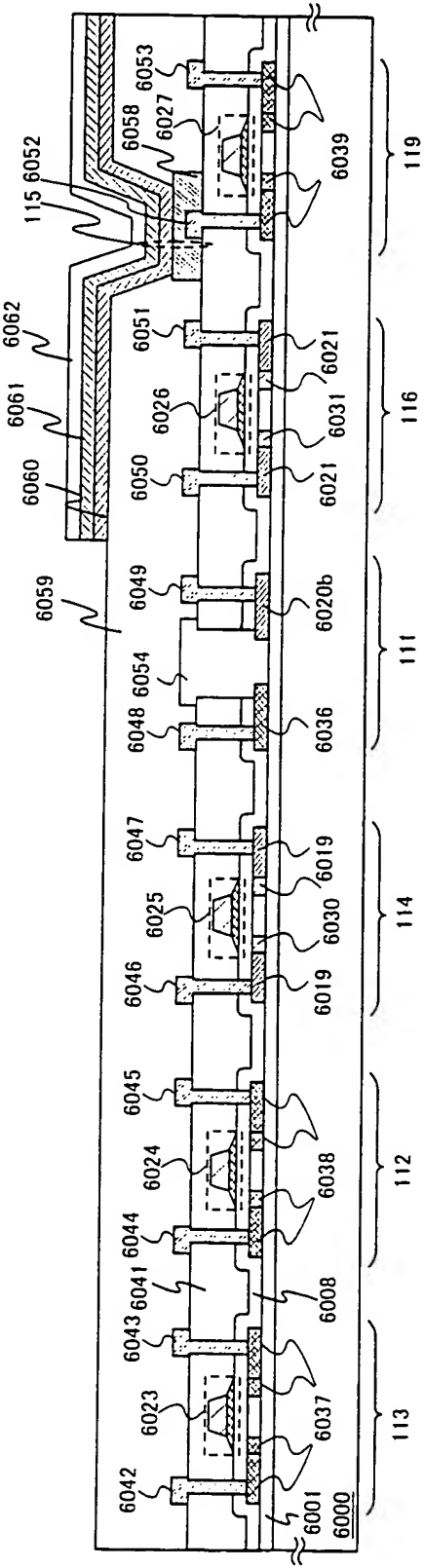


FIG. 16



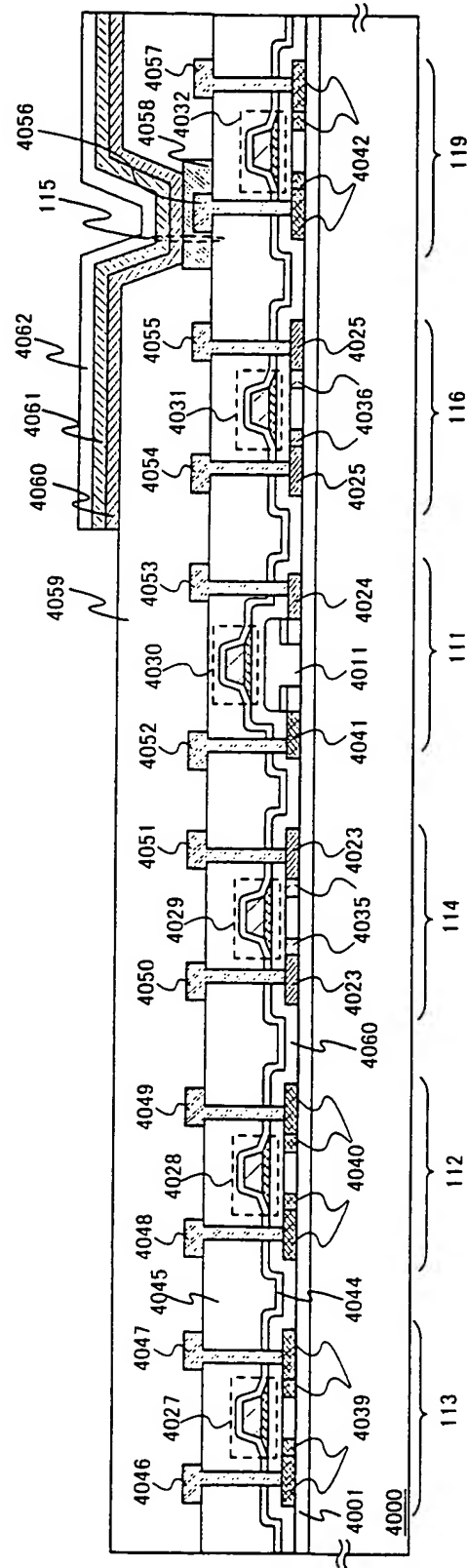


FIG. 17

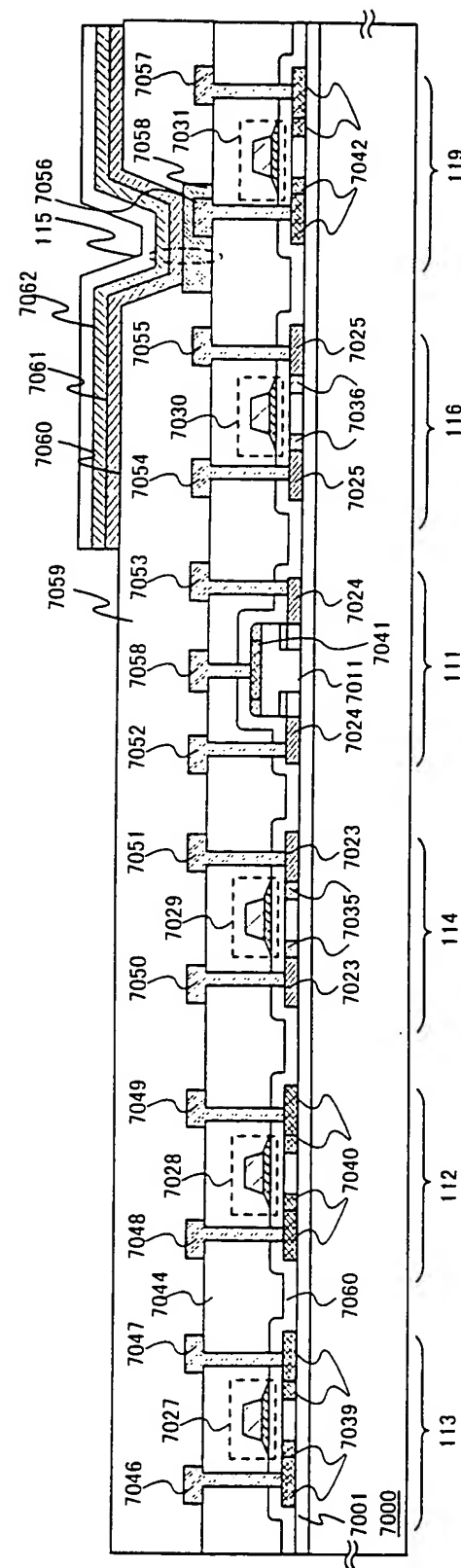


FIG. 18

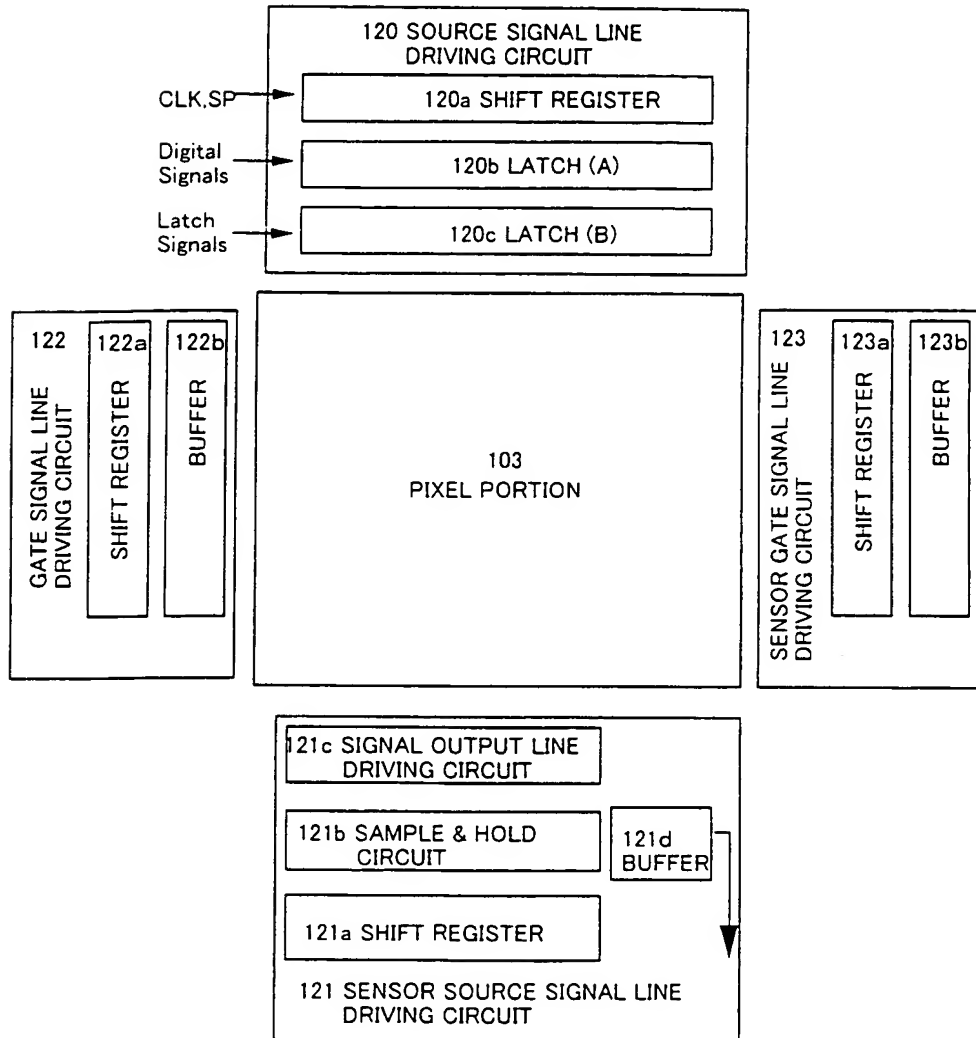


FIG. 19

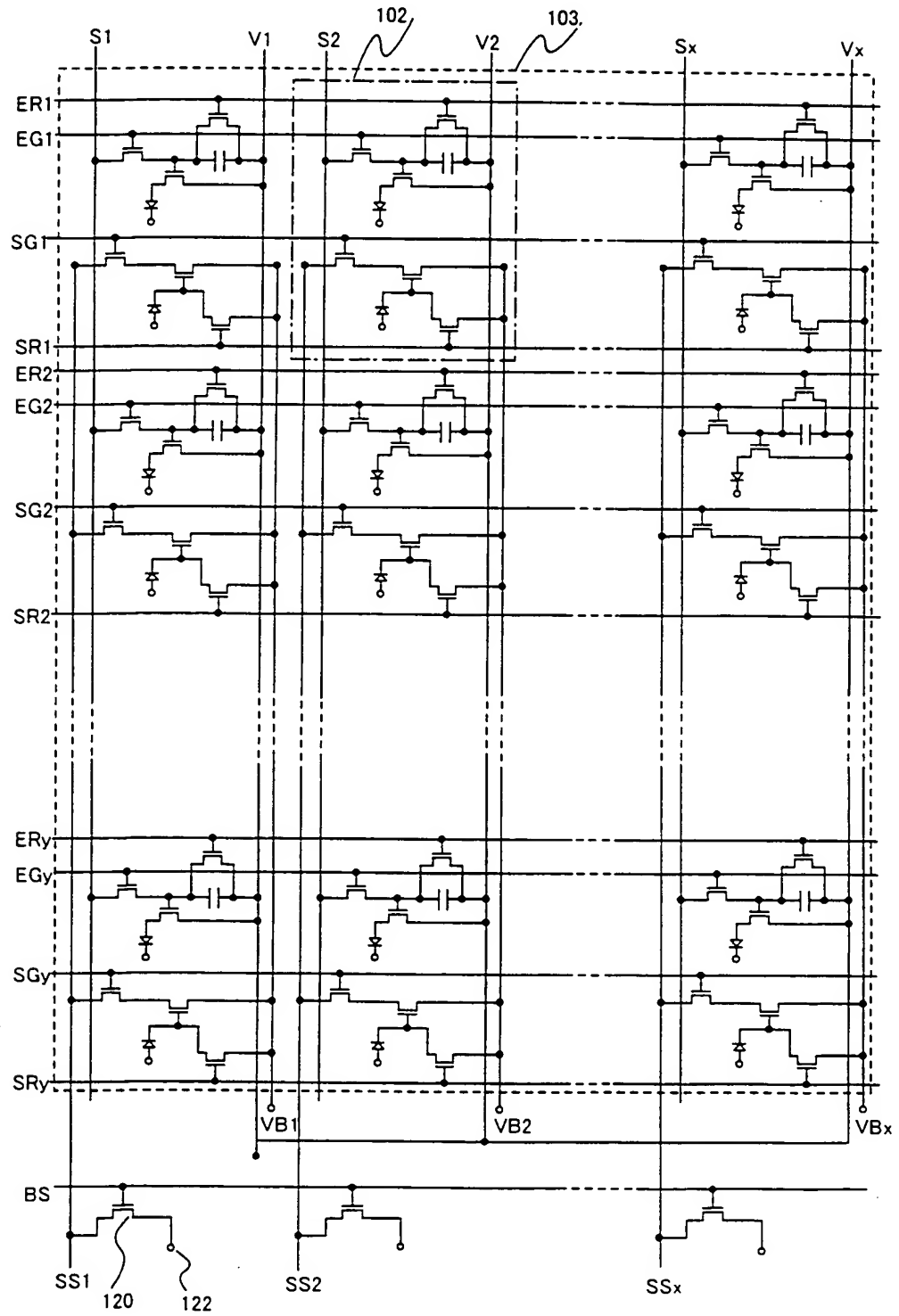


FIG. 20

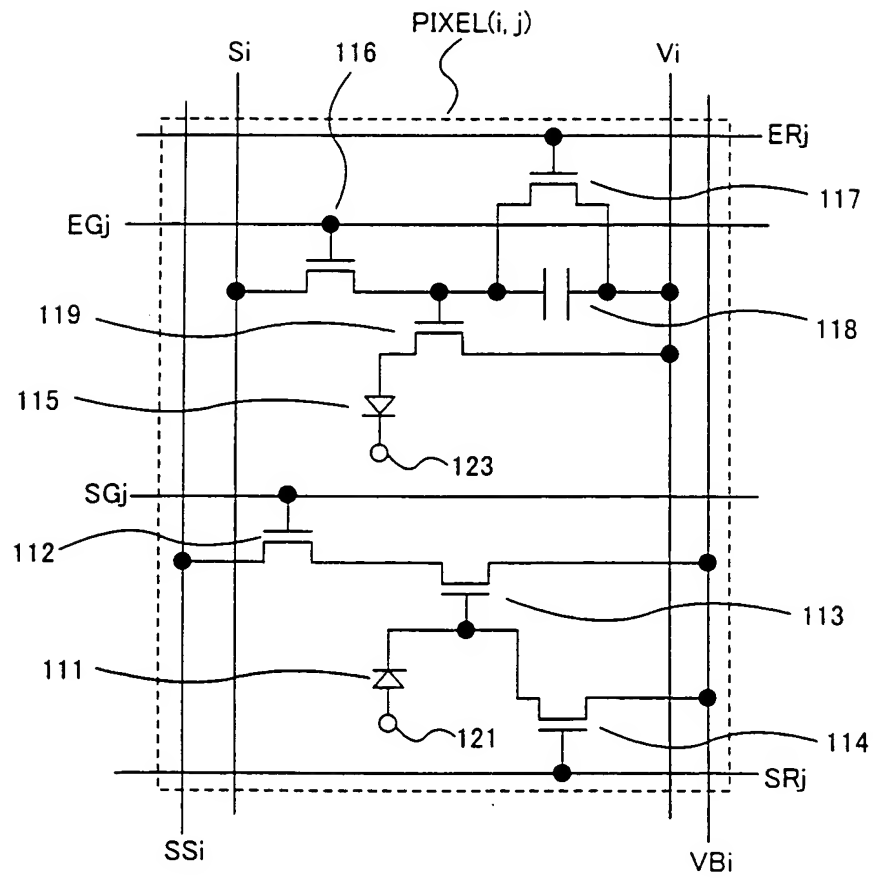


FIG. 21

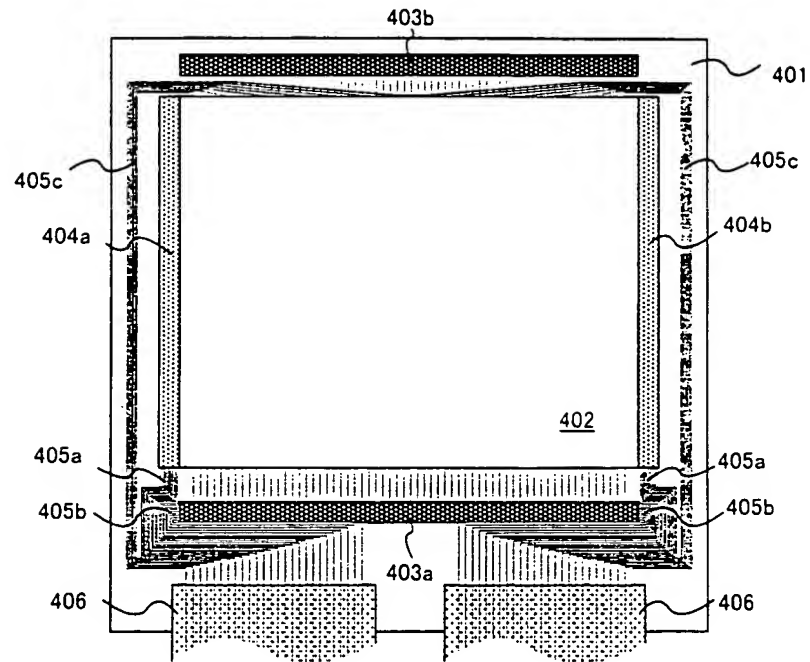


FIG. 22

FIG. 23A

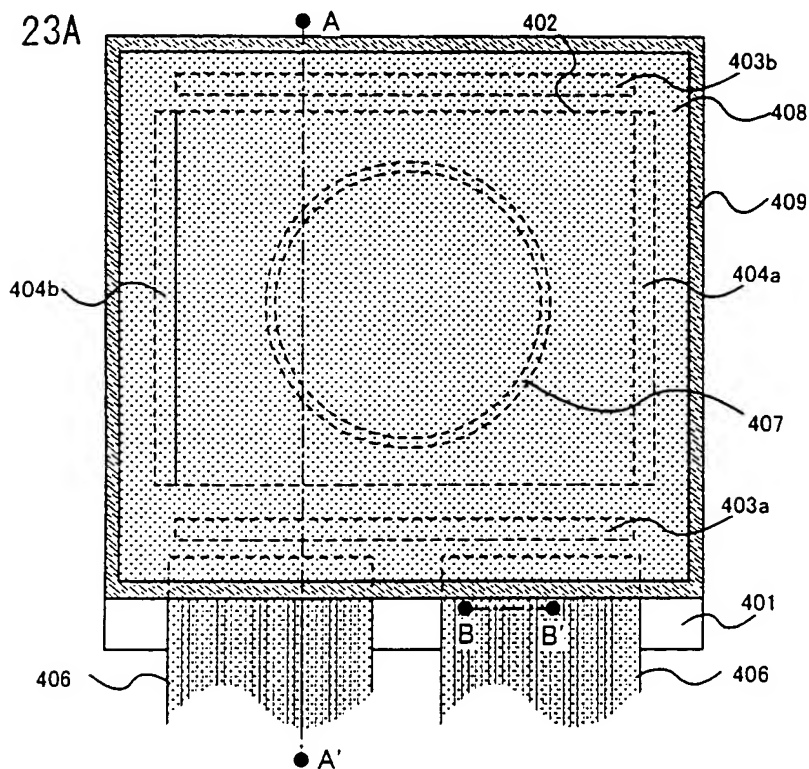


FIG. 23B

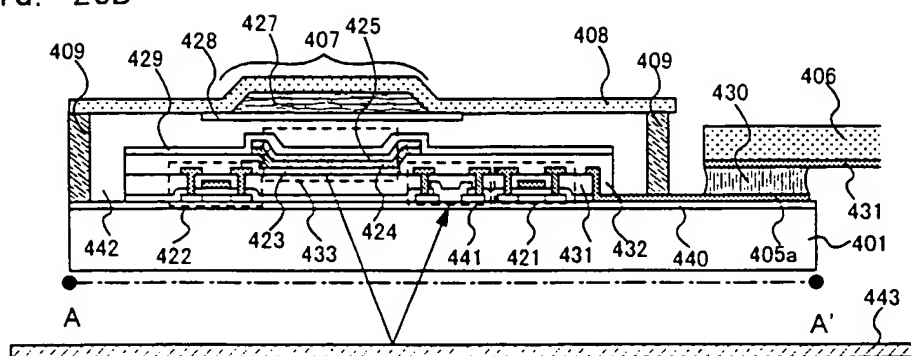


FIG. 23C

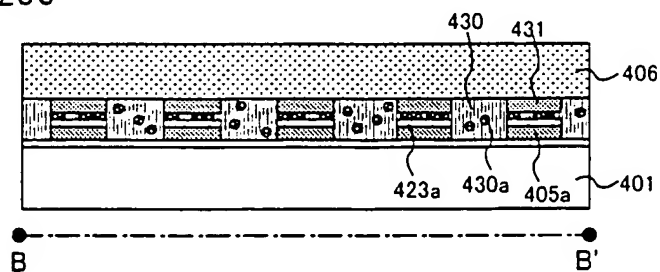


FIG. 24A

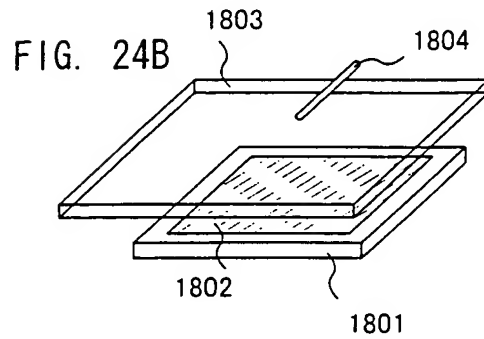
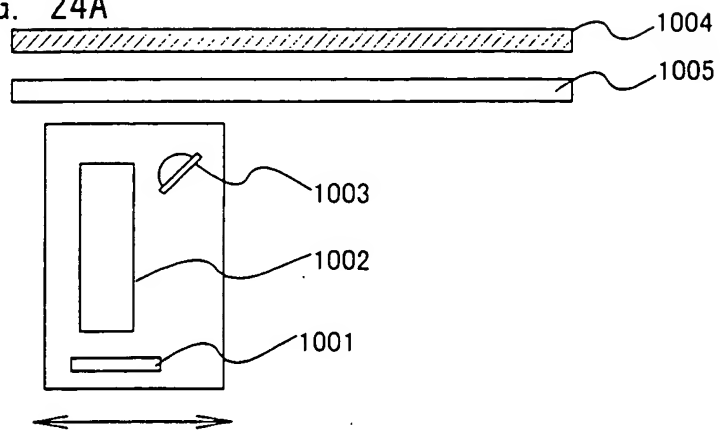


FIG. 24C

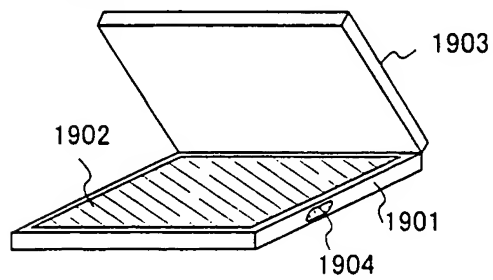


FIG. 24D

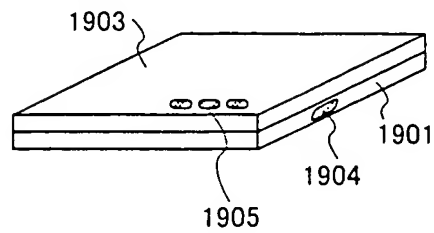




FIG. 25A

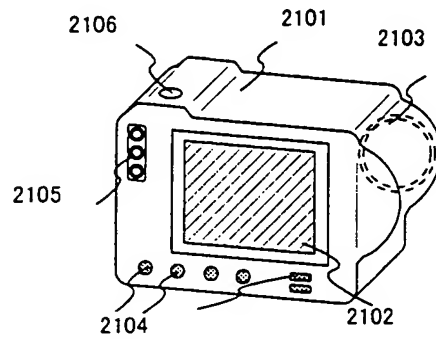


FIG. 25B

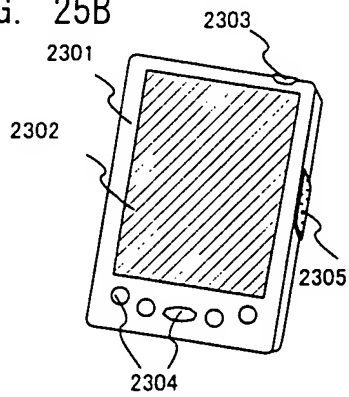


FIG. 25C

